

RD74LVC1G98

Configurable Multiple-Function Gate

REJ03D0730-0100 Rev.1.00 Jul 26, 2006

Description

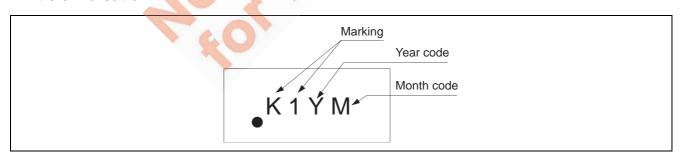
The RD74LVC1G98 has configurable multiple–function gate in a 6-pin package. The Output state is determined by eight patterns of 3-bit input. The user can choose the logic functions AND, NAND, OR, NOR, INVERTER, Non–Inverted Buffer, Data Selector. Low voltage and high-speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

Features

- The basic gate function is lined up as Renesas uni logic series.
- Supply voltage range: 1.65 to 5.5 V
- Operating temperature range: –40 to +85°C
- All inputs V_{IH} (Max.) = 5.5 V (@ V_{CC} = 0 V to 5.5 V)
- All outputs V_0 (Max.) = 5.5 V (@ V_{CC} = 0 V)
- Output current: $\pm 4 \text{ mA} (@V_{CC} = 1.65 \text{ V})$
 - $\pm 8 \text{ mA } (@V_{CC} = 2.3 \text{ V})$
 - $\pm 24 \text{ mA } (@V_{CC} = 3.0 \text{ V})$
 - $\pm 32 \text{ mA} (@V_{CC} = 4.5 \text{ V})$
- All the logical input has hysteresis voltage for the slow transition.
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
RD74LVC1G98WPE	WCSP-6 pin	SXBG0006LA-A (TBS-6BV)	WP	E (3,000 pcs/reel)

Article Indication



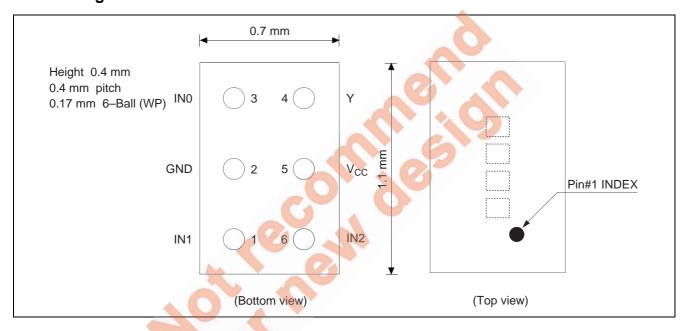
Function Table

	Inputs						
IN2	IN1	IN0	Y				
L	L	L	Н				
L	L	Н	Н				
L	Н	L	L				
L	Н	Н	L				
Н	L	L	Н				
Н	L	Н	L				
Н	Н	L	Н				
Н	Н	Н	L				

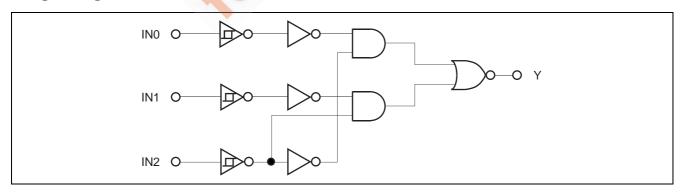
H: High level

L: Low level

Pin Arrangement



Logic Diagram

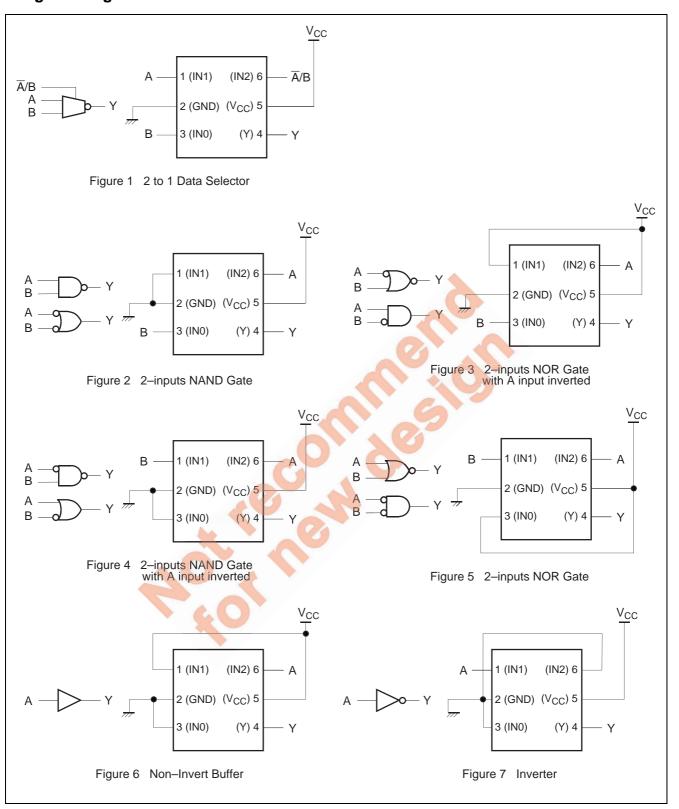


Function Selection Table

Logic Function	Figure No.
2 to 1 data Selector	1
2-inputs NAND	2
2-inputs NOR with one input inverted	3
2-inputs AND with one input inverted	3
2-inputs NAND with one input inverted	4
2-inputs OR with one input inverted	4
2-inputs NOR	5
Non-Invert Buffer	6
Inverter	7



Logic Configurations



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V _{CC}	-0.5 to 6.5	V	
Input voltage range *1	VI	-0.5 to 6.5	V	
Output voltage range *1, 2	Vo	-0.5 to $V_{CC} + 0.5$	V	Output : H or L
Output voltage range	V _O	-0.5 to 6.5] v	V _{CC} : OFF
Input clamp current	I _{IK}	-50	mA	V ₁ < 0
Output clamp current	I _{OK}	-50	mA	V _O < 0
Continuous output current	I _O	±50	mA	$V_O = 0$ to V_{CC}
Continuous current through V _{CC} or GND	I _{CC} or I _{GND}	±100	mA	
Package Thermal impedance	θ_{ja}	123	°C/W	WP
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 5.5 V maximum.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	Vcc	1.65	5.5	V	
Input voltage range	Vı	0	5.5	V	
Output voltage range	Vo	0	V _{CC}	V	
			4		V _{CC} = 1.65 V
			8		$V_{CC} = 2.3 \text{ V}$
	I _{OL}	_	16		V _{CC} = 3.0 V
		- 1	24		VCC = 3.0 V
Output current	40		32	mA	$V_{CC} = 4.5 \text{ V}$
Output current			-4	IIIA	V _{CC} = 1.65 V
			-8		$V_{CC} = 2.3 \text{ V}$
_ (Іон	_	-16		V _{CC} = 3.0 V
			-24		VCC = 3.0 V
			-32		V _{CC} = 4.5 V
Operating free-air temperature	Tal	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

Electrical Characteristics

 $Ta = -40 \text{ to } 85^{\circ}C$

Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	Test condition
		1.8	0.8	_	1.4		
	V _T ⁺	2.5	1.2	_	1.7		
	VΤ	3.3	1.6		2.3		
		5.0	2.3		3.0		
		1.8	0.4		0.7		
Threshold voltage	V _T	2.5	0.6		1.0	V	
Trireshold voltage	VΤ	3.3	0.9	1	1.4	V	
		5.0	1.5		2.0		
		1.8	0.4		0.7		
	ΔV_{T}	2.5	0.4		0.8		
	Δντ	3.3	0.4	_	0.9		
		5.0	0.4	_	1.0		
		1.65 to 5.5	V _{CC} -0.1	_			$I_{OH} = -100 \mu A$
	V _{ОН}	1.65	1.2	_	-		$I_{OH} = -4 \text{ mA}$
		2.3	1.9	_			$I_{OH} = -8 \text{ mA}$
		3.0	2.4		7 (4)	1	$I_{OH} = -16 \text{ mA}$
			2.3	-			$I_{OH} = -24 \text{ mA}$
Output voltage		4.5	3.8		9-1	V	$I_{OH} = -32 \text{ mA}$
Output voltage		1.65 to 5.5	-		0.1	V	$I_{OL} = 100 \mu A$
		1.65	-		0.45		$I_{OL} = 4 \text{ mA}$
	V _{OL}	2.3	-	<u> </u>	0.3		$I_{OL} = 8 \text{ mA}$
	VOL	3.0		-	0.4		$I_{OL} = 16 \text{ mA}$
		5.0			0.55		$I_{OL} = 24 \text{ mA}$
		4.5)	0.55		$I_{OL} = 32 \text{ mA}$
Input current	I _{IN}	0 to 5.5			±5	μΑ	$V_{IN} = 5.5 \text{ V or GND}$
	Icc	5.5			10		$V_{IN} = V_{CC}$ or GND,
Quiescent	100	0.0			10		$I_0 = 0$
supply current						μΑ	One input at V _{CC} -0.6 V,
	ΔI_{CC}	3 to 5.5		_	500		Other input at V _{CC} or
					40		GND
Output leakage current	l _{OFF}	0	_		±10	μA	V_{IN} or $V_O = 0$ to 5.5 V
Input capacitance	C _{IN}	3.3		3.5	_	pF	$V_{IN} = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

 $V_{CC}=1.8{\pm}0.15~V$

Itam	Symbol Ta = -40 to 85°C		to 85°C	l lmi4	Test Conditions	FROM	ТО
Item	Symbol	Min	Max	Unit	rest Conditions	(Input)	(Output)
Propagation delay time	t _{PLH} t _{PHL}	3.2	14.4	l ns	$C_L = 30 \text{ pF},$ $R_L = 1.0 \text{ k}\Omega$	IN	Υ

 $V_{CC} = 2.5 \pm 0.2 \text{ V}$

ltom	Cumbal	Ta = -40 to 85°C		l lmi4	Test Conditions	FROM	ТО
Item	Symbol	Min	Max	Unit	rest Conditions	(Input)	(Output)
Propagation delay time	t _{PLH} t _{PHL}	2.0	8.3	ns	$C_L = 30 \text{ pF},$ $R_L = 500 \Omega$	IN	Υ

 $V_{CC} = 3.3 \pm 0.3 \text{ V}$

Item	Symbol	Ta = -40	Ta = -40 to 85°C		Test Conditions	FROM	ТО
item	Syllibol	Min	Max	Unit	rest Conditions	(Input)	(Output)
Propagation delay time	t _{PLH} t _{PHL}	1.5	6.3	ns	$C_L = 50 \text{ pF},$ $R_L = 500 \Omega$	IN	Y

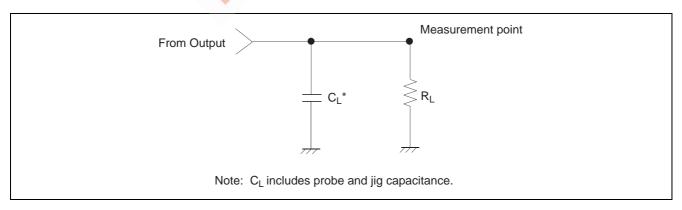
 $V_{CC} = 5.0 \pm 0.5 \text{ V}$

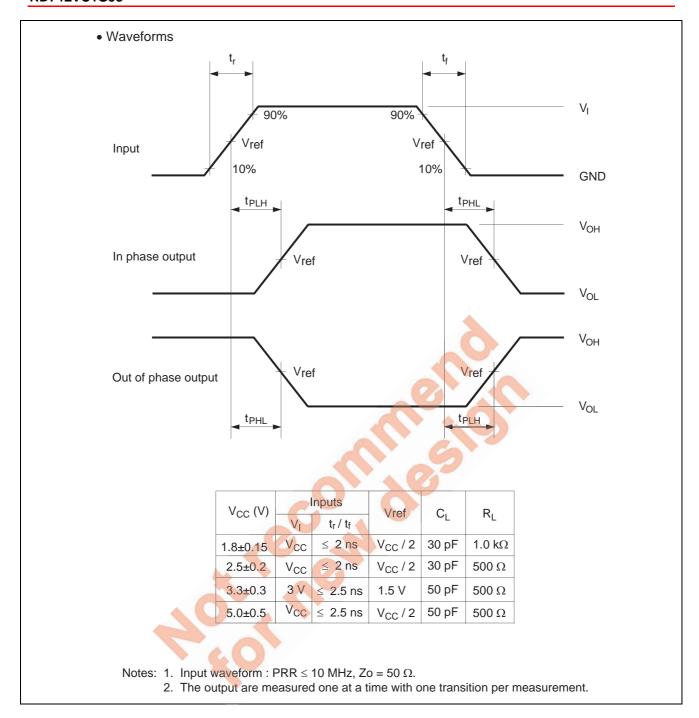
Item	Symbol	Ta = -40	Ta = −40 to 85°C		Test Conditions	FROM	ТО
	Symbol	Min	Max	Unit	rest conditions	(Input)	(Output)
Propagation delay time	t _{PLH} t _{PHL}	1.1	5.1	ns	$C_L = 50 \text{ pF},$ $R_L = 500 \Omega$	IN	Υ

Operating Characteristics

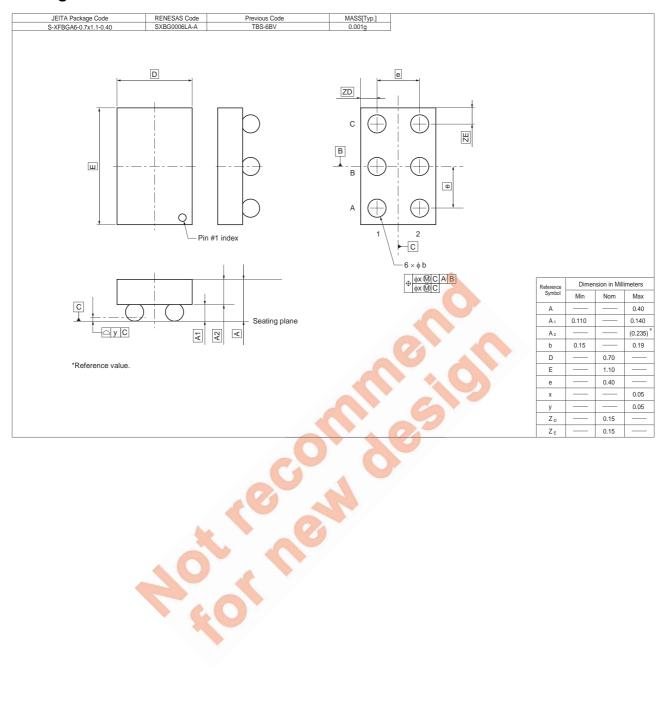
Item	Symbol	V _{cc} (V)	13	Ta = 25°C		Unit	Test Conditions	
item	Symbol	VCC (V)	Min	Тур	Max	Ollit	rest Conditions	
	X . *	1.8	—	23	_			
Dower dissipation consistence	C _{PD}	2.5	_	23	_	nE	f _ 10 M⊔→	
Power dissipation capacitance		3.3	_	23	_	pF	f = 10 MHz	
		5.0	_	26	_			

Test Circuit





Package Dimensions



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